Bo Keun Park

List of Publications by Year
in descending order

85	1,174	430874	434195
papers	citations	18 h-index	31 g-index

86	86	86	1426
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Strategic allocation of two-dimensional van der Waals semiconductor as an oxygen reservoir for boosting resistive switching reliability. Applied Surface Science, 2022, 577, 151936.	6.1	2
2	Synthesis and Characterization of New Strontium Complexes with Multidentate Ligands. ChemistrySelect, 2022, 7, .	1.5	1
3	Novel Heteroleptic Tin(II) Complexes Capable of Forming SnO and SnO₂ Thin Films Depending on Conditions Using Chemical Solution Deposition. ACS Omega, 2022, 7, 1232-1243.	3.5	6
4	Atomic layer deposition of a ruthenium thin film using a precursor with enhanced reactivity. Journal of Materials Chemistry C, 2021, 9, 3820-3825.	5.5	11
5	Synthesis of novel volatile niobium precursors containing carboxamide for Nb2O5 thin films. Polyhedron, 2021, 200, 115134.	2.2	4
6	Atomic-layer-deposited SnO film using novel Sn(dmamb)2 precursor for p-channel thin film transistor. Applied Surface Science, 2021, 547, 148758.	6.1	15
7	Synthesis of Heteroleptic Zinc Complexes Containing Aminoalkoxide and Î² â€Diketonate Ligands. ChemistrySelect, 2021, 6, 5880-5884.	1.5	1
8	Synthesis and Crystal Structures of New Strontium Complexes with Aminoalkoxy and Î²-Diketonato Ligands. ACS Omega, 2021, 6, 15948-15956.	3.5	2
9	Synthesis of New Heteroleptic Indium Complexes as Potential Precursors for Indium Oxide Thin Films. European Journal of Inorganic Chemistry, 2021, 2021, 2480-2485.	2.0	2
10	Synthesis of Novel Unsymmetric Strontium Complexes Containing Aminoalkoxides. ChemistrySelect, 2021, 6, 7823-7828.	1.5	2
11	New Volatile Tantalum Imido Precursors with Carboxamide Ligands. ACS Omega, 2021, 6, 24795-24802.	3.5	0
12	Trimesitylborane-embedded radical scavenging separator for lithium-ion batteries. Current Applied Physics, 2021, 31, 1-6.	2.4	2
13	Atomic Layer Deposition of Cu₂SnS₃ Thin Films: Effects of Composition and Heat Treatment on Phase Transformation. Chemistry of Materials, 2021, 33, 8112-8123.	6.7	6
14	Group IV Transition Metal (M = Zr, Hf) Precursors for High-Î° Metal Oxide Thin Films. Inorganic Chemistry, 2021, 60, 17722-17732.	4.0	4
15	Polycrystalline and high purity SnO2 films by plasma-enhanced atomic layer deposition using H2O plasma at very low temperatures of 60â€“90ÂÂ°C. Vacuum, 2021, , 110739.	3.5	1
16	Atomic layer deposition of pure In2O3 films for a temperature range of 200â€“300â€¯Â°C using heteroleptic liquid In(DMAMP)2(OiPr) precursor. Ceramics International, 2020, 46, 3139-3143.	4.8	14
17	Strategy of solution process precursors for phase change memory. Polyhedron, 2020, 176, 114289.	2.2	6
18	Synthesis and characterization of tungsten Imido/Aminoalkoxide complexes to deposit tungsten oxide thin films. Inorganica Chimica Acta, 2020, 502, 119307.	2.4	2

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19	Effect of Oxygen Source on the Various Properties of SnO2 Thin Films Deposited by Plasma-Enhanced Atomic Layer Deposition. Coatings, 2020, 10, 692.	2.6	16
20	Heteroleptic manganese compounds as potential precursors for manganese based thin films and nanomaterials. RSC Advances, 2020, 10, 29659-29667.	3.6	1
21	Synthesis and characterization of novel zinc precursors for ZnO thin film deposition by atomic layer deposition. Dalton Transactions, 2020, 49, 4306-4314.	3.3	6
22	Indium complexes with aminothiolate ligands as single precursors for indium chalcogenides. Inorganica Chimica Acta, 2020, 505, 119504.	2.4	5
23	Tin(II) Aminothiolate and Tin(IV) Aminothiolate Selenide Compounds as Single-Source Precursors for Tin Chalcogenide Materials. Inorganic Chemistry, 2020, 59, 3513-3517.	4.0	10
24	Simultaneous etching of underlying metal oxide and sulfide thin films during Cu2S atomic layer deposition. Applied Surface Science, 2020, 524, 146452.	6.1	9
25	Synthesis and Structure of Tin and Germanium Complexes as Precursors Containing Alkoxyaminoalkoxide Ligands for Thin Film Transistors. European Journal of Inorganic Chemistry, 2020, 2020, 2074-2079.	2.0	1
26	Highly efficient photocatalytic methylene blue degradation over Sn(O,S)/TiO2 photocatalyst fabricated via powder atomic layer deposition of SnO and subsequent sulfurization. Materials Letters, 2020, 272, 127868.	2.6	4
27	A facile synthetic route to tungsten diselenide using a new precursor containing a long alkyl chain cation for multifunctional electronic and optoelectronic applications. RSC Advances, 2019, 9, 6169-6176.	3.6	5
28	Synthesis of noble molybdenum and tungsten complexes for hydrocracking catalyst of heavy oil. Journal of Industrial and Engineering Chemistry, 2019, 72, 408-413.	5.8	9
29	Phase-controlled SnO2 and SnO growth by atomic layer deposition using Bis(N-ethoxy-2,2-dimethyl) Tj ETQq1 1 0.784314 rgBT /Over	4.8	42
30	Band gap engineering of atomic layer deposited Zn_xSn_{1â€x}O buffer for efficient Cu(In,Ga)Se₂ solar cell. Progress in Photovoltaics: Research and Applications, 2018, 26, 745-751.	8.1	13
31	Optimized Method for Lowâ€Energy and Highly Reliable Multibit Operation in a HfO₂â€Based Resistive Switching Device. Advanced Electronic Materials, 2018, 4, 1800261.	5.1	12
32	Growth of Cu2S thin films by atomic layer deposition using Cu(dmamb)2 and H2S. Applied Surface Science, 2018, 456, 501-506.	6.1	11
33	Synthesis of Indium Complexes for Thin Film Transistor Applications Bearing N â€Alkoxy Carboxamide Ligands. ChemistrySelect, 2018, 3, 6691-6695.	1.5	5
34	Synthesis and Structure of Novel Tin Complexes Containing Aminoalkoxide Ligands. ChemistrySelect, 2018, 3, 7836-7839.	1.5	2
35	Indium complexes bearing donor-functionalized alkoxide ligands as precursors for indium oxide thin films. Journal of Organometallic Chemistry, 2017, 833, 43-49.	1.8	7
36	Germanium Compounds Containing Geâ•E Double Bonds (E = S, Se, Te) as Single-Source Precursors for Germanium Chalcogenide Materials. Inorganic Chemistry, 2017, 56, 4084-4092.	4.0	19

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37	Fourâ€Bitsâ€Perâ€Cell Operation in an HfO₂â€Based Resistive Switching Device. Small, 2017, 13, 1701781.	10.0	37
38	New Heteroleptic Cobalt Precursors for Deposition of Cobalt-Based Thin Films. ACS Omega, 2017, 2, 5486-5493.	3.5	7
39	Thermal atomic layer deposition of In2O3 thin films using dimethyl(N-ethoxy-2,2-dimethylcarboxylicpropanamide)indium and H2O. Applied Surface Science, 2017, 419, 758-763.	6.1	30
40	Ruthenocene Precursors for Ruthenium-Containing Thin-Film Deposition: An Example of Solvent Nucleophilic Attack on Fulvene. Organometallics, 2017, 36, 2755-2760.	2.3	3
41	Atomic layer deposition of indium oxide thin film from a liquid indium complex containing 1-dimethylamino-2-methyl-2-propoxy ligands. Applied Surface Science, 2016, 383, 1-8.	6.1	19
42	Low-Temperature Growth of Indium Oxide Thin Film by Plasma-Enhanced Atomic Layer Deposition Using Liquid Dimethyl(N-ethoxy-2,2-dimethylpropanamido)indium for High-Mobility Thin Film Transistor Application. ACS Applied Materials & Interfaces, 2016, 8, 26924-26931.	8.0	59
43	Trinuclear magnesium complexes stabilized by aminoalkoxide ligands. Journal of Coordination Chemistry, 2016, 69, 2591-2597.	2.2	0
44	N-Alkoxy Carboxamide Stabilized Tin(II) and Germanium(II) Complexes for Thin-Film Applications. European Journal of Inorganic Chemistry, 2016, 2016, 5539-5546.	2.0	18
45	Synthesis and characterization of triosmium-bis[60]fullerene and bis(metal cluster)[60]fullerene compounds. Molecular Crystals and Liquid Crystals, 2016, 636, 155-158.	0.9	0
46	Highly-conformal nanocrystalline molybdenum nitride thin films by atomic layer deposition as a diffusion barrier against Cu. Journal of Alloys and Compounds, 2016, 663, 651-658.	5.5	33
47	Growth of tantalum nitride film as a Cu diffusion barrier by plasma-enhanced atomic layer deposition from bis((2-(dimethylamino)ethyl)(methyl)amido)methyl(tert-butylimido)tantalum complex. Applied Surface Science, 2016, 362, 176-181.	6.1	16
48	Synthesis of Monoâ€Imido Tungsten Complexes Directly from WCl₆. ChemistrySelect, 2016, 1, 44-48.	1.5	4
49	Synthesis of novel tin complexes using functionalized oxime ligands. Inorganica Chimica Acta, 2016, 446, 1-5.	2.4	3
50	Synthesis and characterization of Mo and W compounds containing aminothiolate ligand for disulfide materials. Polyhedron, 2015, 100, 199-205.	2.2	3
51	Hexaâ€coordinated Strontium Silylamide Complex Stabilized by Tetradentate Alkoxy Ligand. Bulletin of the Korean Chemical Society, 2015, 36, 2587-2588.	1.9	1
52	New heteroleptic magnesium complexes for MgO thin film application. Dalton Transactions, 2015, 44, 2103-2109.	3.3	19
53	Highly Conformal Amorphous Wâ€“Siâ€“N Thin Films by Plasma-Enhanced Atomic Layer Deposition as a Diffusion Barrier for Cu Metallization. Journal of Physical Chemistry C, 2015, 119, 1548-1556.	3.1	17
54	Improved Initial Growth Behavior of SrO and SrTiO₃ Films Grown by Atomic Layer Deposition Using {Sr(demamp)(tmhd)}₂ as Sr-Precursor. Chemistry of Materials, 2015, 27, 3881-3891.	6.7	32

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55	Heteroleptic magnesium complexes containing amidinate and aminoalkoxy ligands. Polyhedron, 2015, 101, 185-190.	2.2	8
56	Heteroleptic strontium complexes stabilized by donor-functionalized alkoxide and Î²-diketonate ligands. Dalton Transactions, 2015, 44, 14042-14053.	3.3	3
57	Synthesis of new heteroleptic strontium complexes stabilized by Î²-ketoiminato ligands. Inorganica Chimica Acta, 2015, 436, 118-122.	2.4	9
58	Atomic Layer Deposition of Ruthenium and Ruthenium Oxide Thin Films from a Zero-Valent (1,5-Hexadiene)(1-isopropyl-4-methylbenzene)ruthenium Complex and O₂. Chemistry of Materials, 2014, 26, 7083-7090.	6.7	37
59	Synthesis and Characterization of Fullerene-Metal Compound with Long Alkyl Chain for Liquid Crystals, Supramolecules, and Optoelectronic Materials. Molecular Crystals and Liquid Crystals, 2014, 600, 35-38.	0.9	1
60	Synthesis, characterization, and electrochemical study ofÂOs3(CO)7(1,2-dppm)(Î¼3-Î·2:Î·2:Î·2-C60) and Os3(CO)7(1,1-dppm)(Î¼3-Î·2:Î·2:Î·2-C60). Journal of Organometallic Chemistry, 2014, 763-764, 20-25.	1.8	3
61	Growth of p-Type Tin(II) Monoxide Thin Films by Atomic Layer Deposition from Bis(1-dimethylamino-2-methyl-2propoxy)tin and H₂O. Chemistry of Materials, 2014, 26, 6088-6091.	6.7	76
62	Synthesis of new heteroleptic strontium complexes. Dalton Transactions, 2014, 43, 14461-14469.	3.3	5
63	Heteroleptic Group 2 Metal Precursors for Metal Oxide Thin Films. European Journal of Inorganic Chemistry, 2014, 2014, 2002-2010.	2.0	29
64	Hydrothermal synthesis of CuInSe2 nanoparticles in acetic acid. Journal of Physics and Chemistry of Solids, 2013, 74, 867-871.	4.0	11
65	Synthesis of Heteroleptic Strontium Complexes Containing Substituted Cyclopentadienyl and Î²-Diketonate Ligands. Bulletin of the Korean Chemical Society, 2013, 34, 967-970.	1.9	5
66	Synthesis and Characterization of Novel Volatile Imido-Aminoalkoxide Tantalum Compounds. Organometallics, 2012, 31, 8109-8113.	2.3	9
67	Physical/chemical properties of tin oxide thin film transistors prepared using plasma-enhanced atomic layer deposition. Materials Research Bulletin, 2012, 47, 3052-3055.	5.2	29
68	Method for Synthesis of Tetrabenzoporphyrin Precursor for Use in Organic Electronic Devices. Journal of Organic Chemistry, 2012, 77, 8329-8331.	3.2	18
69	Synthesis and structure of novel strontium complexes of unsymmetrically functionalized Î²-diketimine ligands. Inorganica Chimica Acta, 2012, 383, 67-71.	2.4	3
70	Synthesis and Structural Characterization of Strontium Complex of Symmetrically Functionalized Î²-Diketimine Ligand. Bulletin of the Korean Chemical Society, 2012, 33, 2059-2062.	1.9	3
71	Charge-Trapping Characteristics of Al₂O₃/Cu/Al₂O₃ Nanolaminate Structures Prepared Through Atomic Layer Deposition. Journal of Nanoscience and Nanotechnology, 2011, 11, 5887-5891.	0.9	0
72	Synthesis and Characterization of Nickel(II) Aminoalkoxides: Application to Molecular Precursors for MOCVD of Ni Thin Films. European Journal of Inorganic Chemistry, 2011, 2011, 1833-1839.	2.0	17

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73	[60]Fullereneâ€“Metal Cluster Complexes: Understanding Novel Î·¹ and Î·^{2[6:5]} Bonding Modes of Metallofullerenes. European Journal of Inorganic Chemistry, 2010, 2010, 1530-1535.	2.0	7
74	Remarkably Efficient Photocurrent Generation Based on a [60]Fullereneâ€“Triosmium Cluster/Znâ€“Porphyrin/Boronâ€“Dipyrrin Triad SAM. Chemistry - A European Journal, 2010, 16, 5586-5599.	3.3	54
75	Synthesis of Ruthenium Pentamethyl[60]fullerene Complexes Bearing Monodentate Diphenylphosphino-methane, -ferrocene, and -butane Ligands. Bulletin of the Korean Chemical Society, 2010, 31, 697-699.	1.9	3
76	Preparation and Optical Properties of Colloidal, Monodisperse, and Highly Crystalline ITO Nanoparticles. Chemistry of Materials, 2008, 20, 2609-2611.	6.7	105
77	[Os3(CO)6(PMe3)3](Î¼3-Î·2:Î·2:Î·2-C60)[Re3(Î¼-H)3(CO)9]: A Fullerene[60] Coordinated to Two Different Trinuclear Clusters. Angewandte Chemie - International Edition, 2007, 46, 1436-1439.	13.8	24
78	Cyclic voltammetry modeling, geometries, and electronic properties for metallofullerene complexes withÎ¼3-Î·2:Î·2:Î·2-C60bonding mode. Journal of Computational Chemistry, 2007, 28, 1100-1106.	3.3	4
79	Synthetic, Electrochemical, and Theoretical Studies of Tetrairidium Clusters Bearing Mono- and Bis[60]fullerene Ligands. Journal of the American Chemical Society, 2006, 128, 11160-11172.	13.7	34
80	Syntheses, Structures, and Electrochemical Properties of Os3(CO)9-n(CNCH2Ph)n(Î¼3-Î·2:Î·2:Î·2-C60) (n= 2â^'4). Organometallics, 2006, 25, 4634-4642.	2.3	13
81	The synthesis and characterization of Re3(Î¼-H)3(CO)9â^'n(PMe3)n(Î¼3-Î·2:Î·2:Î·2-C60) (n=2,3) complexes. Journal of Organometallic Chemistry, 2005, 690, 4704-4711.	1.8	11
82	Ortho Phosphorylation of PPh3To Give a Diphosphine and Formation of a â€œButterflyâ€•Structure on a Tetrairidium Framework. Organometallics, 2005, 24, 675-679.	2.3	17
83	Novel[60]Fullerene-Assistedortho-Phosphanation on a Tetrairidium Butterfly Framework. Angewandte Chemie - International Edition, 2004, 43, 1712-1714.	13.8	17
84	Cluster and Polynuclear Compounds. Inorganic Syntheses, 2004, , 184-232.	0.3	3
85	Two Metal Centers Bridging Two C60Cages as a Wide Passage for Efficient Interfullerene Electronic Interaction. Journal of the American Chemical Society, 2003, 125, 13920-13921.	13.7	53